




Faculty Profile

Title	Ms.	First Name	Mansi	Last Name	Agrawal	Photograph
Designation		Assistant Professor				
Address (Office)		D-907, Grand Ajnara Heritage, Sector 74, Noida				
Contact No. (Mobile)		9350048587				
Email		mansiagra2000@gmail.com				
EDUCATIONAL QUALIFICATIONS						
Degree		Institution				Year
PhD		Indian Institute of Technology Delhi				Pursuing
M.Sc.		St. Stephen's College, University of Delhi				2008
B.Sc. (H)		Miranda House, University of Delhi				2006
CAREER PROFILE						
Assistant Professor, Department of Physics, Gargi College 20.07.2016- till date						
Assistant Professor, Department of Physics, Deen Dayal Upadhyaya College 30.07.2014 - 19.07.2016						
Senior Research Fellow, Solid State Physics Laboratory, DRDO Sept.2011-July 2014						
Junior Research Fellow, Solid State Physics Laboratory, DRDO Sept. 2009-Sept. 2011						
ADMINISTRATIVE ASSIGNMENTS						
AREAS OF INTEREST / SPECIALIZATION						
Material Science & Nanotechnology						
SUBJECT TAUGHT						
Physics of Devices & Communication, Analog Systems & Applications, Mechanics, Electricity & Magnetism, Basic Instrumentation Skills, Waves & Optics, Mathematical Physics Scilab, Quantum Mechanics & Applications Scilab, Statistical Mechanics Scilab						
RESEARCH GUIDANCE						
REFRESHER COURSE/ORIENTATION PROGRAMME/FACULTY DEVELOPMENT PROGRAMMES ATTENDED:						
1. Attended FDP program on “UG Level Computational Physics Practical Using Python” organised by Birjhora Mahavidyalaya, Gauhati held virtually from 04 Jan- 09 Jan. 2021.						
2. Attended DBT sponsored FDP program on “Introduction to Scilab” held at Hansraj College, University of Delhi 22 Sept. – 23 Sept. 2017.						

PUBLICATIONS PROFILE

1. “Structural and vibrational properties of CVD grown few layers MoS₂ on catalyst free PAMBE grown GaN nanowires on Si (111) substrates”, **Mansi Agrawal**, Anubha Jain, Vishakha Kaushik, Akhilesh Pandey, B.R. Mehta and R. Muralidharan, Journal of Alloys and Compounds, 861 (2021) 157965.
2. “Nano harvesting of GaN nanowires on Si (211) substrates by plasma assisted molecular beam epitaxy”, **Mansi Agrawal**, Anubha Jain, D. V. Sridhara Rao, Akhilesh Pandey, Anshu Goyal, Anand Kumar, Sushil Lamba, B.R. Mehta, K. Muraleedharan and R. Muralidharan, Journal of Crystal Growth, 402 (2014) 37-41.

INTERNATIONAL/NATIONAL CONFERENCES/SEMINARS/SYMPOSIA

1. Mansi Agrawal, Anubha Jain, Janesh Kaushik, B.R. Mehta and R. Muralidharan, "AlGaIn/GaN circular high electron mobility transistors", International Conference on Thin Films and Nanotechnology: Knowledge, Leadership, & Commercialization (ICTN-KLC), 24-26 Aug. 2021, Indian Institute of Technology Delhi (Oral).
2. Mansi Agrawal, Anubha Jain, B. R. Mehta and R. Muralidharan, "Plasma assisted molecular beam epitaxy grown GaN nanowires on Si (211) substrates for UV sensing applications", International Conference on Emerging Electronics (ICEE-2020), 26– 28 Nov. 2020, Indian Institute of Technology Delhi (Poster).
3. Mansi Agrawal, Anubha Jain, Akhilesh Pandey B. R. Mehta and R. Muralidharan, "Catalyst free growth of GaN nanowires on Si (111) substrates by plasma assisted molecular beam epitaxy", International Conference on Emerging Advancement in Science and Technology (ICEAST 2019), 5-6 Sept. 2019, Manekshaw Centre, New Delhi, India (Poster).
4. Mansi Agrawal, Anubha Jain, Poornendu Chaturvedi, B.R. Mehta, and R. Muralidharan, "Self Induced GaN nanowires on Si(211) substrates for Nox Sensing Applications", International Conference Nanoscience and Nanotechnology (ICONSAT-2018), 21-23 March 2018, IISc Bengaluru (Poster). (Awarded Best Poster Presentation)
5. Mansi Agrawal, B.R. Mehta, and R. Muralidharan, "Effect of Surface Treatments on the Evolution of Microstructures in GaN Thin Films and GaN/AlGaIn/GaN Heterostructures", XIX International Workshop on Physics of Semiconductor Devices (IWPSD-2017), 11-15 Dec. 2017, Indian Institute of Technology Delhi (Poster).
6. Mansi Agrawal, Janesh Kaushik, B.R. Mehta and R. Muralidharan, "AlGaIn/GaN circular high electron mobility transistors on Si(111) substrates for sensing applications", 9th International Conference on Materials for Advanced Technologies (ICMAT-2017), 18-23 June 2017, Suntec Exhibition and Convention Centre, Singapore (Oral).
7. Mansi Agrawal, B.R. Mehta and R. Muralidharan, National Workshop on III-Nitride Materials and Devices, "Growth of GaN nanowires on Si (211) substrates by plasma assisted molecular beam epitaxy", 12-13 Dec. 2013, Solid State Physics Laboratory, Delhi (Oral).
8. Mansi Agrawal, Anand Kumar and B.R. Mehta, "Effect of hot H₃PO₄ etching in GaN thin films and AlGaIn/GaN heterostructures", ICMS and Cambridge University Winter School 2012: Frontiers of Materials Science, 3 -8 Dec. 2012 JNCASR, Bangalore (Poster).

RESEARCH PROJECTS (MAJOR GRANTS/RESEARCH COLLABORATION)

AWARDS AND DISTINCTIONS

CSIR-NET JRF, 2009

ASSOCIATION WITH PROFESSIONAL BODIES

OTHER ACTIVITIES

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